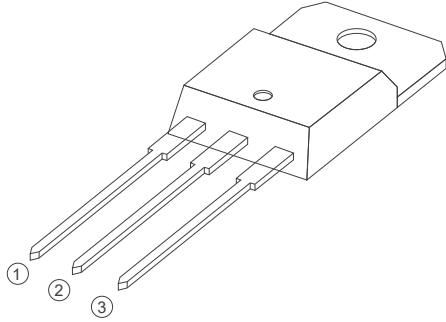
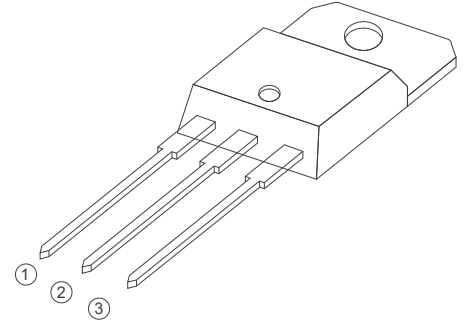


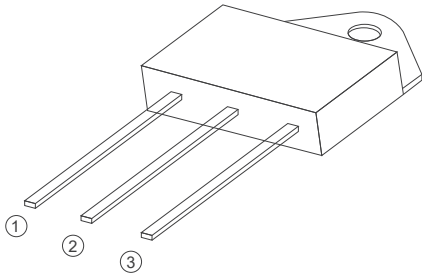
BTA/BTB26 Series
25A TRIACs
3 Quadrants
4 Quadrants



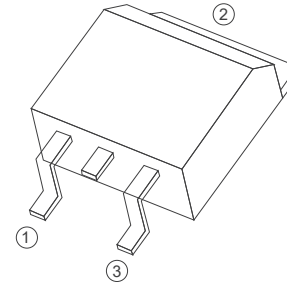
TO-220A Insulated



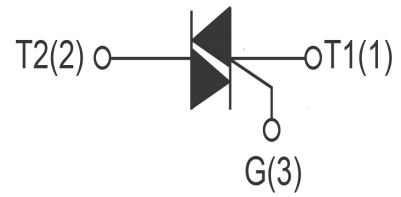
TO-220B Non-Insulated



TO-3P Insulated



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FEATURES

> $I_T(RMS)$: 25A > V_{GT} : 1.5V > V_{DRM} V_{RRM} : 800V and 1000V

APPLICATIONS

Washing machine, vacuums, massager, solid state relay, AC Motor speed regulation and so on.

Absolute Maximum Ratings (T_J=25°C unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Unit
VDRM VRRM	Repetitive Peak Off-State Voltage	BTA26-800	800	V
		BTA26-1000	1000	V
IT(RMS)	R.M.S On-State Current	T _c =110°C	25	A
ITSM	Surge On-State Current	tp=16.7ms/tp=10ms	280/300	A
I ² t	I ² t for fusing	Tp=10ms	520	A ² s
PG(AV)	Average Gate Power Dissipation	T _J =125°C	1	W
IGM	Peak Gate Current	T _J =125°C	6	A
T _J	Operating Junction Temperature		~40~125	°C
TSTG	Storage Temperature		~40~150	°C

Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Conditions	Value			Unit
			CW	BW	B	
IDRM	Repetitive Peak Off-State Current	T _J =25°C	5			uA
		T _J =125°C	3			mA
IRRM	Repetitive Peak Reverse Current	T _J =25°C	5			uA
		T _J =125°C	3			mA
VTM	Forward "on" voltage	IT=35A tp=380us	1.55			V
VGT	Gate trigger voltage	VD=12V ,RL=30Ω	≤1.5			V
di/dt	Critical rate of rise of on-state current	I,II,III F=120Hz,T _J =125°C IV IG=2xIGT,tr≤100ns	≥50			A/us
			≥10			A/us
IGT	Gate trigger current	I,II,III VD=12V RL=30Ω IV	≤35	≤50	≤50	mA
			/	/	≤100	mA
IH	Holding current	IT=0.2A	≤60	≤80	≤80	mA
V _{DG}	Gate non-trigger voltage	ALL VD=VDRM T _J =125°C	≥0.2			V
dv/dt	Critical-rate of rise of commutation voltage	T _J =125°C VD=2/3VDRM Gate	≥400	≥1000	≥500	V/us
R _{th(j-c)}	Thermal resistance	Junction to case	1.1			°C/W
R _{th(j-a)}	Thermal resistance	Junction to ambient	50			°C/W

FIG1

Maximum power dissipation versus RMS on-state current

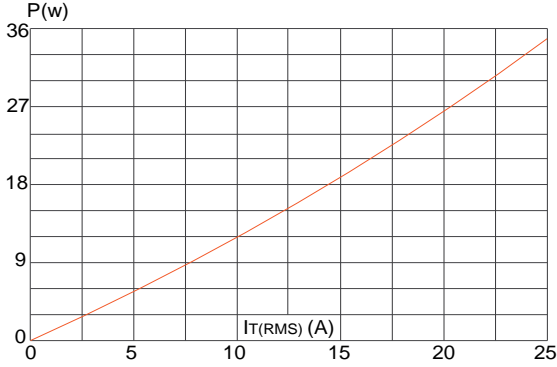


FIG2

RMS on-state current versus case temperature

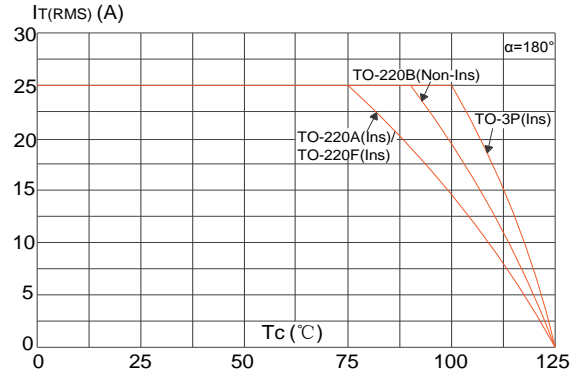


FIG3

Surge peak on-state current versus number of cycles

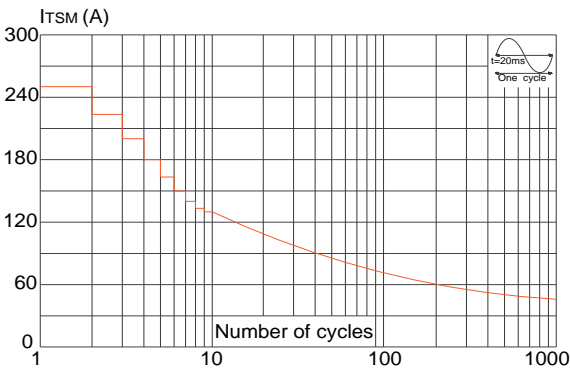


FIG4

On-state characteristics (maximum values)

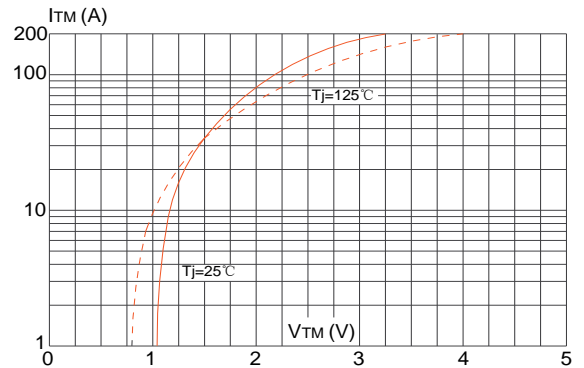


FIG5

Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t ($di/dt < 100\text{A}/\mu\text{s}$)

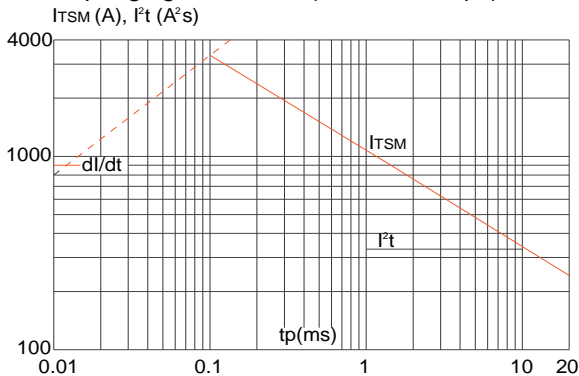
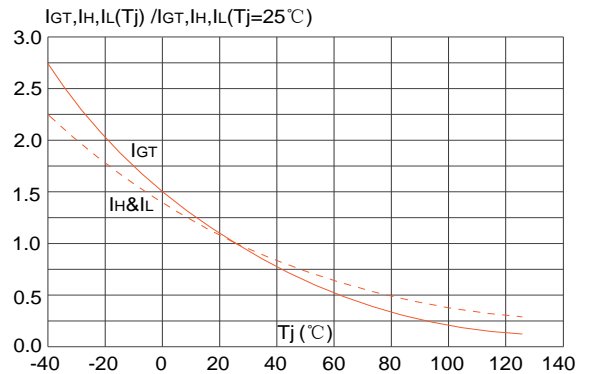
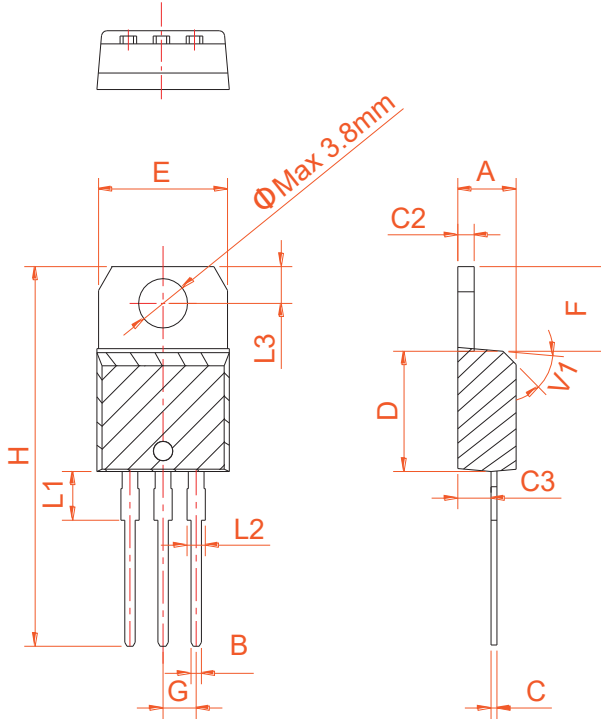


FIG6

Relative variations of gate trigger current, holding current and latching current versus junction temperature



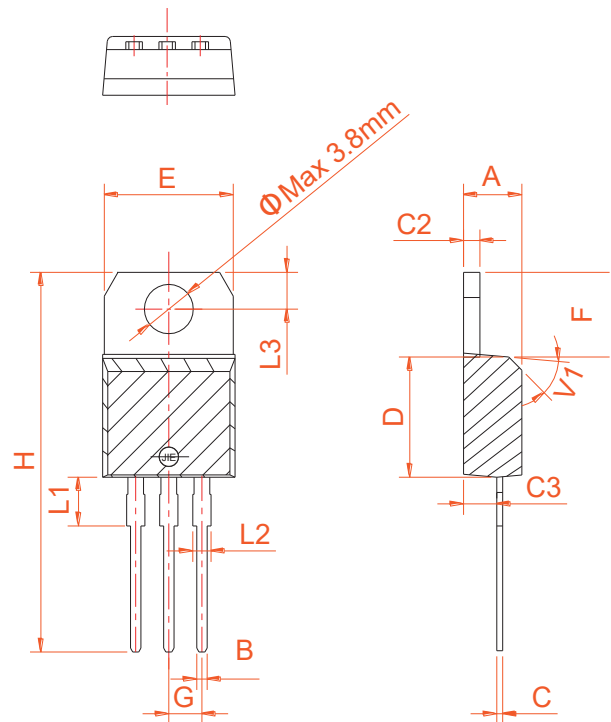
PACKAGE MECHANICAL DATA



TO-220A Ins

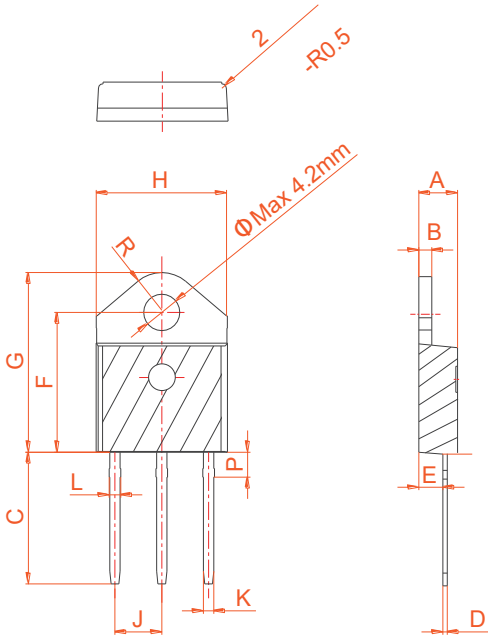
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.80		10.4	0.386		0.409
F	6.55		6.95	0.258		0.274
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.60		10.4	0.378		0.409
F	6.20		6.60	0.244		0.260
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	



TO-220B Non-Ins

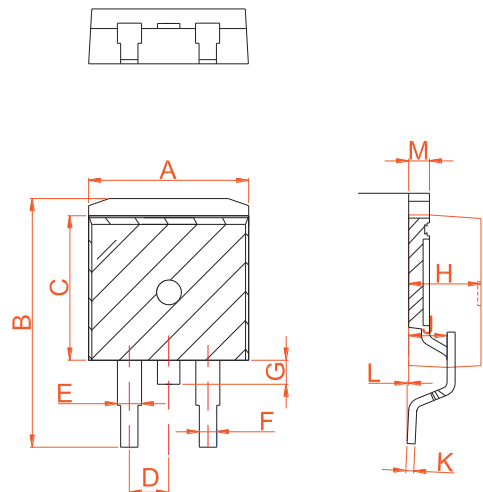
PACKAGE MECHANICAL DATA



TO-3P Ins

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	1.45		1.55	0.057		0.061
C	14.35		15.60	0.565		0.614
D	0.50		0.70	0.020		0.028
E	2.70		2.90	0.106		0.114
F	15.80		16.50	0.622		0.650
G	20.40		21.10	0.803		0.831
H	15.10		15.50	0.594		0.610
J	5.40		5.65	0.213		0.222
K	1.10		1.40	0.043		0.055
L	1.35		1.50	0.053		0.059
P	2.80		3.00	0.110		0.118
R		4.35			0.171	

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90		10.20	0.390		0.402
B	14.70		15.80	0.579		0.622
C	9.4		9.6	0.37		0.378
D		2.54			0.100	
E	1.20		1.40	0.047		0.055
F	0.75		0.85	0.029		0.033
G			1.75			0.069
H	4.40		4.70	0.173		0.185
J	2.30		2.70	0.091		0.106
K	0.38		0.55	0.015		0.022
L	0	0.10	0.25	0	0.004	0.010
M	1.25		1.35	0.049		0.053



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